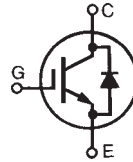


High Voltage, High Gain BIMOSFET™ Monolithic Bipolar MOS Transistor

IXBH 10N170
IXBT 10N170

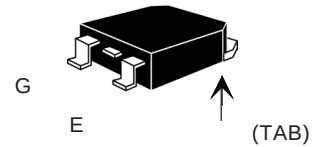
$$\begin{aligned} V_{CES} &= 1700 \text{ V} \\ I_{C25} &= 20 \text{ A} \\ V_{CE(sat)} &= 3.8 \text{ V} \end{aligned}$$

Preliminary Data Sheet

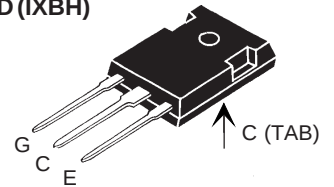


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	1700	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 1 \text{ M}\Omega$	1700	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	20	A
I_{C90}	$T_C = 90^\circ\text{C}$	10	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1 ms	40	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 33 \Omega$ Clamped inductive load	$I_{CM} = 20$ $V_{CES} = 1350$	A V
P_C	$T_C = 25^\circ\text{C}$	140	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
Maximum Lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
Maximum Tab temperature for soldering SMD devices for 10 s		260	$^\circ\text{C}$
M_d	Mounting torque (M3) (TO-247)	1.13/10Nm/lb.in.	
Weight	TO-247 AD	6	g
	TO-268	4	g

TO-268 (IXBT)



TO-247 AD (IXBH)



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Features

- High Blocking Voltage
- JEDEC TO-268 surface and JEDEC TO-247 AD
- Low conduction losses
- High current handling capability
- MOS Gate turn-on - drive simplicity
- Molding epoxies meet UL 94 V-0 flammability classification

Applications

- AC motor speed control
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies
- Capacitor discharge circuits

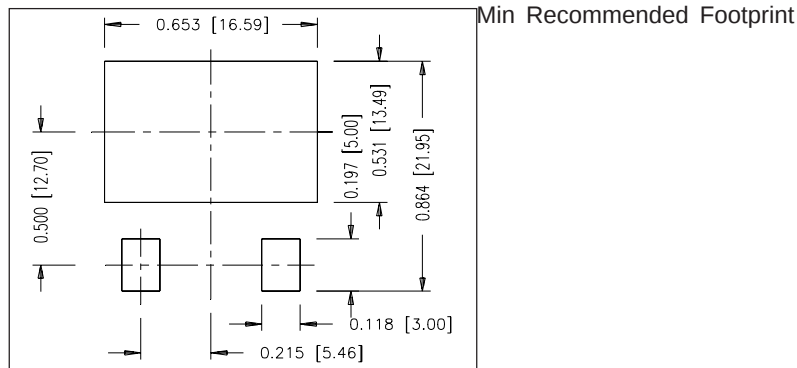
Advantages

- High power density
- Suitable for surface mounting
- Easy to mount with 1 screw, (isolated mounting screw hole)

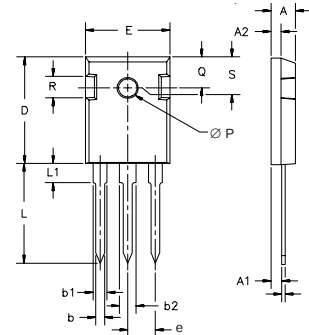
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 250 \mu\text{A}$, $V_{GE} = 0 \text{ V}$ Temperature Coefficient	1700	0.10	V %/K
$V_{GE(th)}$	$I_C = 250 \mu\text{A}$, $V_{CE} = V_{GE}$ Temperature Coefficient	3.0	- 0.24	V %/K
I_{CES}	$V_{CE} = 0.8 V_{CES}$, $V_{GE} = 0 \text{ V}$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$			10 100 μA
I_{GES}	$V_{CE} = 0 \text{ V}$, $V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}$, $V_{GE} = 15 \text{ V}$ $T_J = 125^\circ\text{C}$	3.4 4.1	3.8	V V

Symbol	Test Conditions	Characteristic Values (T _j = 25°C, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	I _C = I _{C90} ; V _{CE} = 10 V, Pulse test, t ≤ 300 μs, duty cycle ≤ 2 %	4.0	6.5	S
C_{ies}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		700	pF
C_{oes}			40	pF
C_{res}			12	pF
Q_g	I _C = I _{C90} ; V _{GE} = 15 V, V _{CE} = 0.5 V _{CES}		30	nC
Q_{ge}			6	nC
Q_{gc}			10	nC
t_{d(on)}	Inductive load, T _j = 25°C I _C = I _{C90} ; V _{GE} = 15 V V _{CE} = 0.8 V _{CES} ; R _G = R _{off} = 56 Ω		35	ns
t_{ri}			28	ns
t_{d(off)}			500	ns
t_{fi}			1000	ns
E_{off}			6	mJ
t_{d(on)}	Inductive load, T _j = 125°C I _C = I _{C90} ; V _{GE} = 15 V V _{CE} = 0.8 V _{CES} ; R _G = R _{off} = 56 Ω		35	ns
t_{ri}			28	ns
E_{on}			0.7	mJ
t_{d(off)}			600	ns
t_{fi}			1200	ns
E_{off}			8	mJ
R_{thJC}				0.89 K/W
R_{thCK}	(TO-247)		0.25	K/W

Symbol	Test Conditions	Characteristic Values (T _j = 25°C, unless otherwise specified)		
		min.	typ.	max.
V_F	I _F = I _{C90} ; V _{GE} = 0 V, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2%			3.0 V
I_{RM}	I _F = I _{C90} ; V _{GE} = 0 V, -di _F /dt = 50 A/μs		10	A
t_{rr}			360	ns

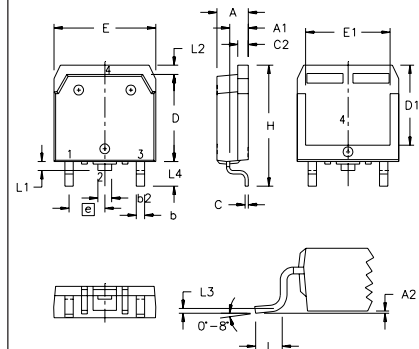


TO-247 AD Outline



Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L ₁		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

TO-268 Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A ₁	.106	.114	2.70	2.90
A ₂	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b ₂	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C ₂	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D ₁	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E ₁	.524	.535	13.30	13.60
e	.215	BSC	5.45	BSC
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L ₁	.047	.055	1.20	1.40
L ₂	.039	.045	1.00	1.15
L ₃	.010	BSC	0.25	BSC
L ₄	.150	.161	3.80	4.10

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1 6,259,123B1 6,306,728B1
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025 6,404,065B1 6,162,665 6,534,343

Fig. 1. Output Characteristics
@ 25 Deg. C

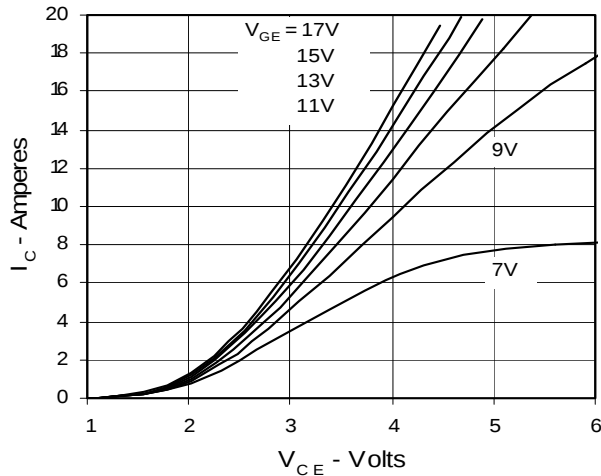


Fig. 2. Extended Output Characteristics
@ 25 deg. C

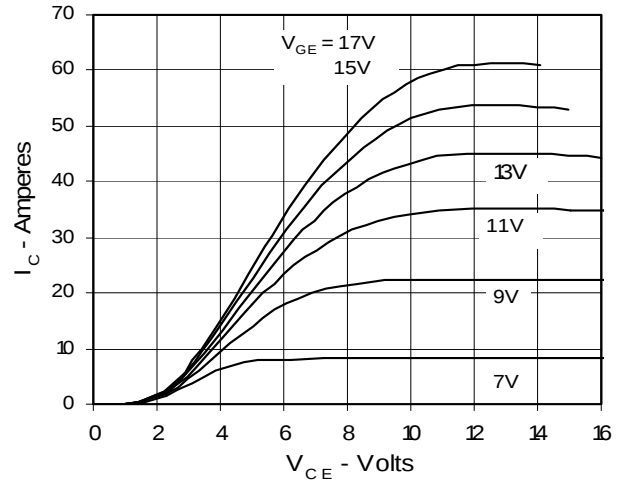


Fig. 3. Output Characteristics
@ 125 Deg. C

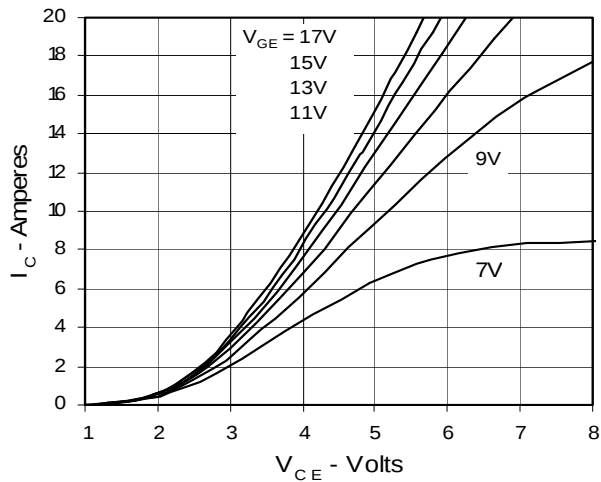


Fig. 4. Temperature Dependence of $V_{CE(sat)}$

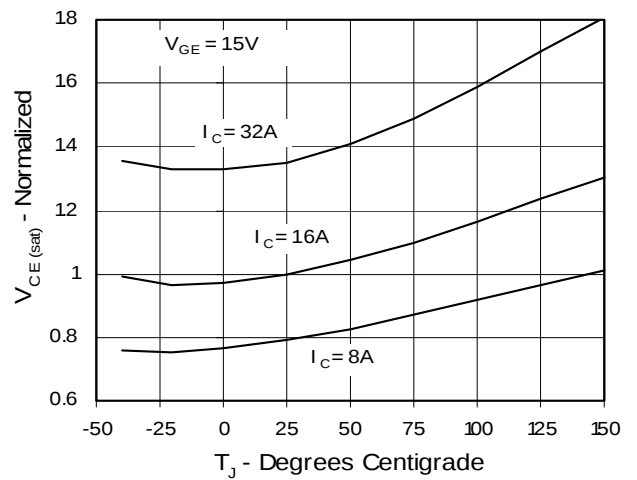


Fig. 5. Collector-to-Emitter Voltage
vs. Gate-to-Emiiter voltage

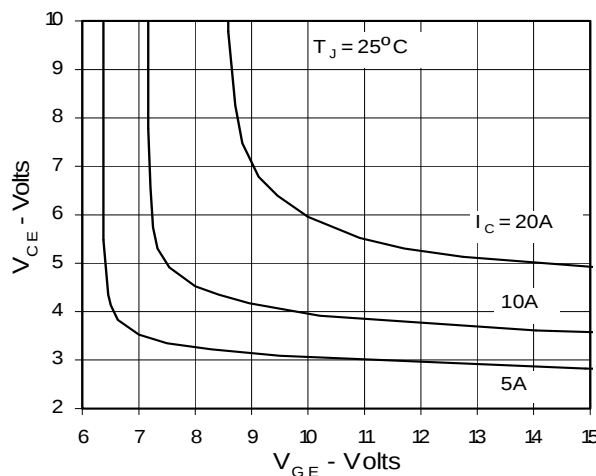


Fig. 6. Input Admittance

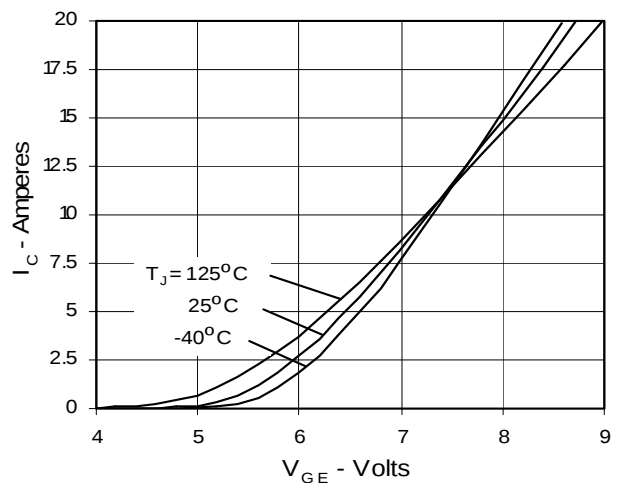


Fig. 7. Transconductance

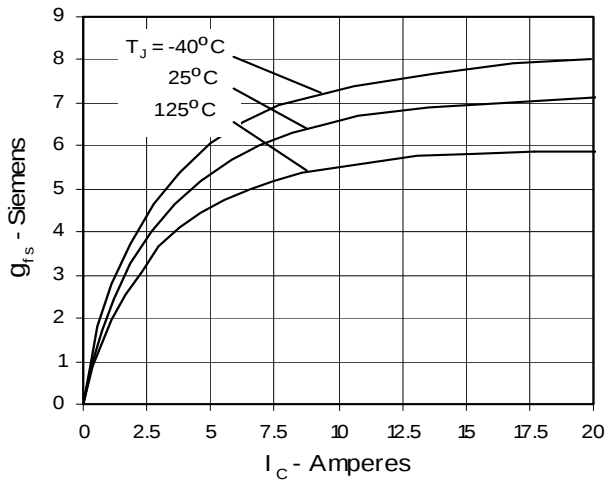


Fig. 8. Forward Voltage Drop of Intrinsic Diode

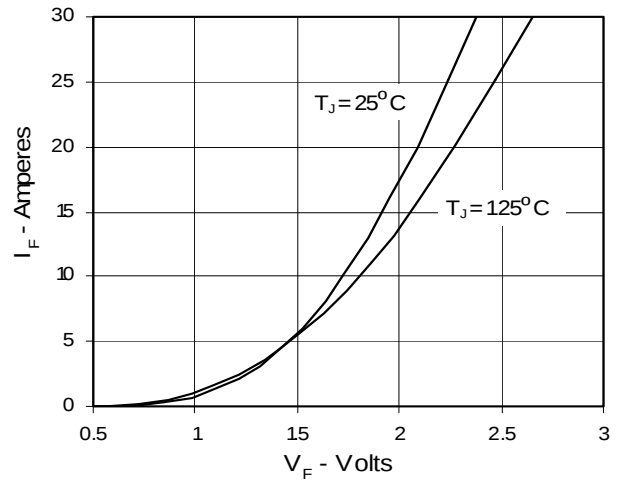


Fig. 9. Dependence of E_{off} on R_G

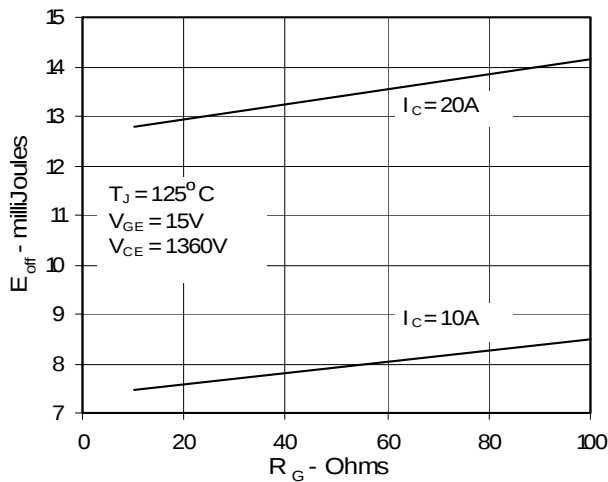


Fig. 10. Dependence of E_{off} on I_C

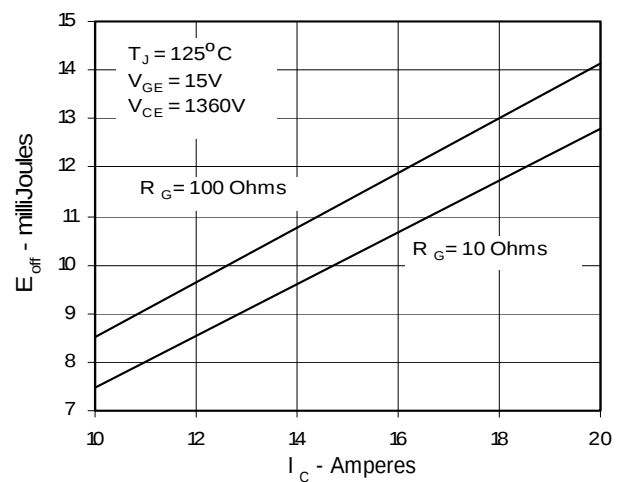


Fig. 11. Dependence of E_{off} on Temperature

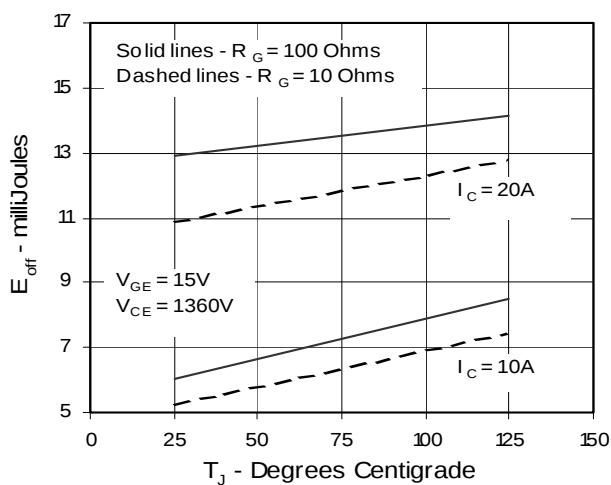
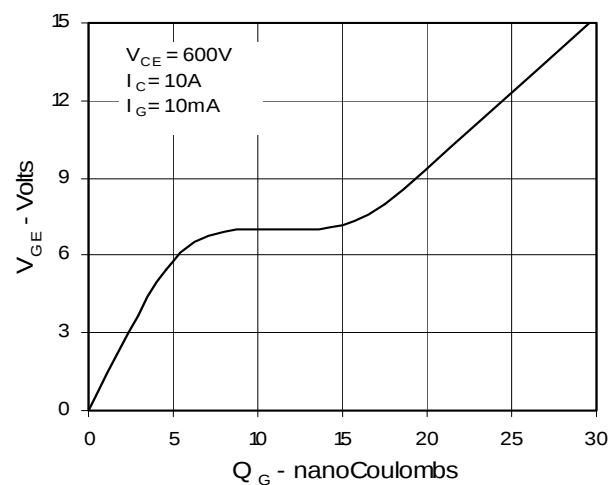


Fig. 12. Gate Charge



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4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025 6,404,065B1 6,162,665 6,534,343

Fig. 12. Capacitance

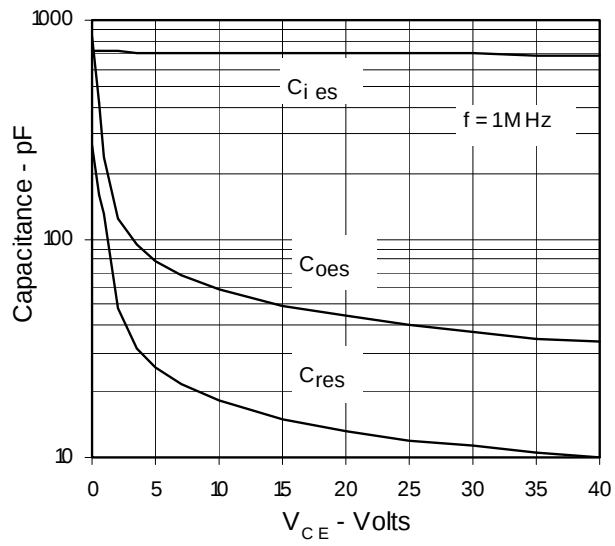


Fig. 13. Maximum Transient Thermal Resistance

